

10V Drive Nch MOSFET

R5019ANX

● Structure

Silicon N-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) High ESD.

● Application

Switching

● Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
R5019ANX		○

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V_{DSS}	500	V	
Gate-source voltage	V_{GSS}	±30	V	
Drain current	Continuous	I_D *3	±19	A
	Pulsed	I_{DP} *1	±76	A
Source current (Body Diode)	Continuous	I_S *3	19	A
	Pulsed	I_{SP} *1	76	A
Avalanche current	I_{AS} *2	9.5	A	
Avalanche energy	E_{AS} *2	24.3	mJ	
Power dissipation	P_D *4	50	W	
Channel temperature	T_{ch}	150	°C	
Range of storage temperature	T_{stg}	-55 to +150	°C	

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 $L = 500 \mu H$, $V_{DD} = 50V$, $R_G = 25 \Omega$, $T_{ch} = 25^\circ C$

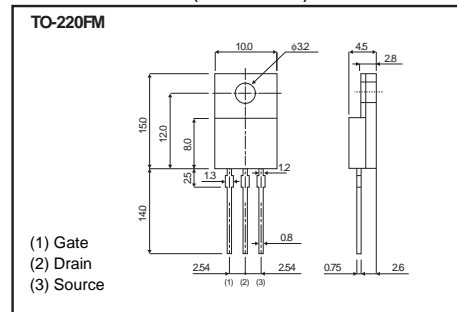
*3 Limited only by maximum temperature allowed.

*4 $T_C = 25^\circ C$

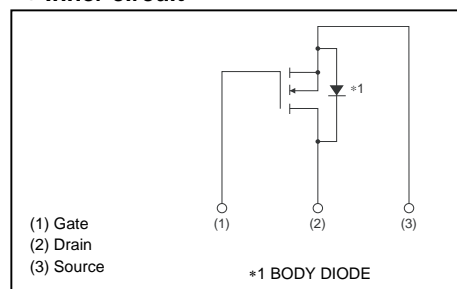
● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th(ch-c)}$	2.5	°C / W

● Dimensions (Unit : mm)



● Inner circuit



● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	100	μA	$V_{DS}=500V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	2.5	-	4.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	0.18	0.24	Ω	$I_D=9.5A, V_{GS}=10V$
Forward transfer admittance	$ Y_{fs} ^*$	6.5	-	-	S	$V_{DS}=10V, I_D=9.5A$
Input capacitance	C_{iss}	-	2050	-	pF	$V_{DS}=25V$
Output capacitance	C_{oss}	-	1200	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	50	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	40	-	ns	$V_{DD}=250V, I_D=9.5A$
Rise time	t_r^*	-	115	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	165	-	ns	$R_L=26.3\Omega$
Fall time	t_f^*	-	100	-	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	-	55	-	nC	$V_{DD}=250V$
Gate-source charge	Q_{gs}^*	-	10	-	nC	$I_D=19A$
Gate-drain charge	Q_{gd}^*	-	24	-	nC	$V_{GS}=10V$

*Pulsed

● Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.5	V	$I_S=19A, V_{GS}=0V$

*Pulsed

●Electrical characteristic curves

Fig.1 Typical Output Characteristics (I)

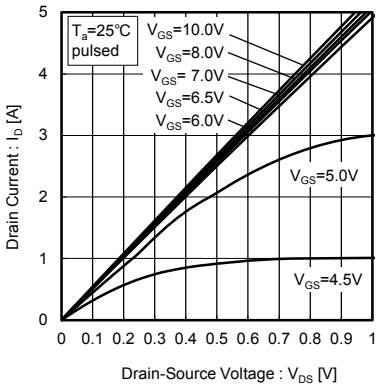


Fig.2 Typical Output Characteristics (II)

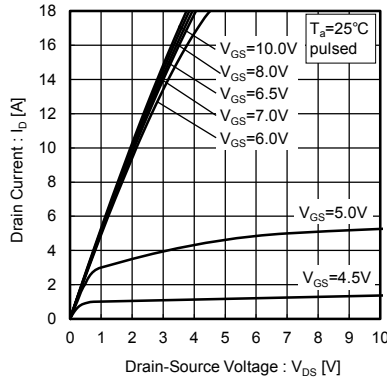


Fig.3 Typical Transfer Characteristics

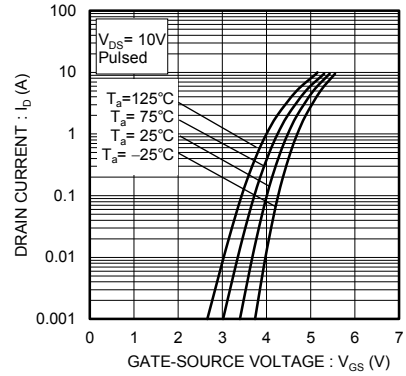


Fig.4 Gate Threshold Voltage vs. Channel Temperature

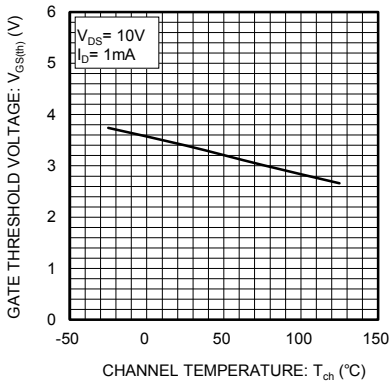


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

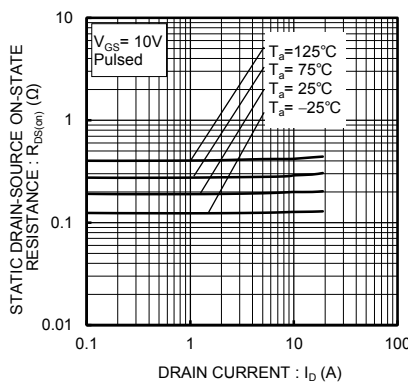


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

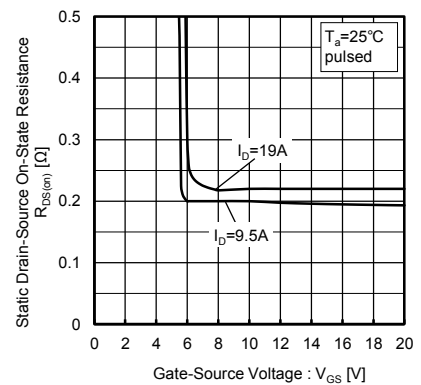


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

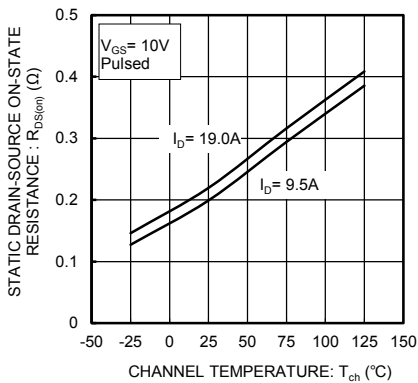


Fig.8 Forward Transfer Admittance vs. Drain Current

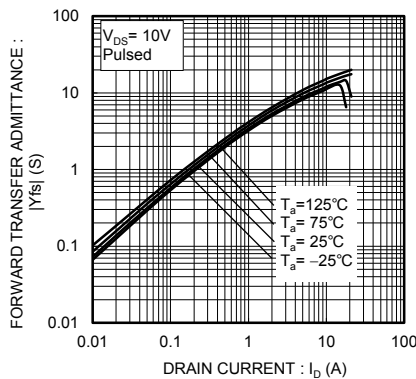


Fig.9 Source Current vs. Source-Drain Voltage

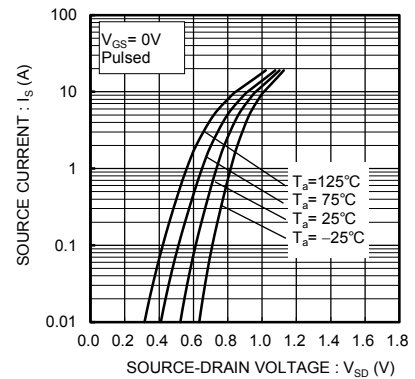


Fig.10 Typical Capacitance vs. Drain-Source Voltage

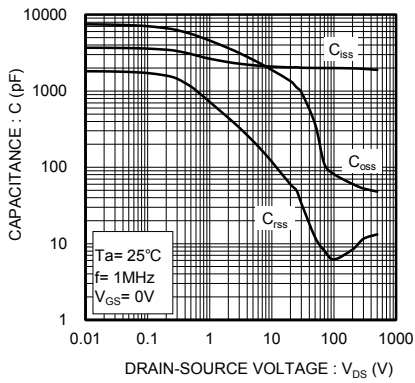


Fig.11 Dynamic Input Characteristics

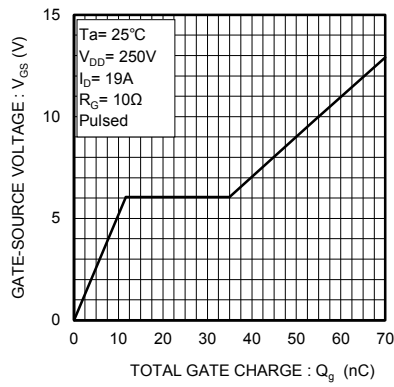


Fig.12 Reverse Recovery Time vs. Source Current

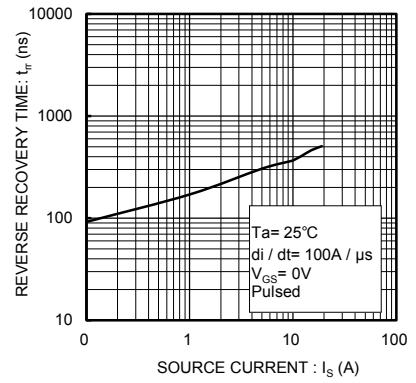
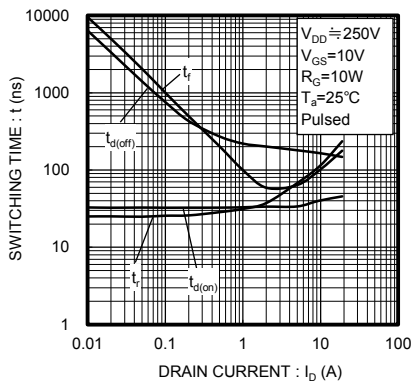


Fig.13 Switching Characteristics



● Measurement circuits

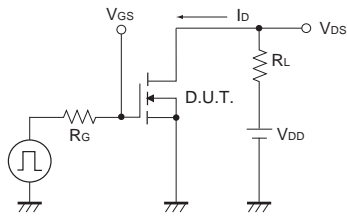


Fig.1-1 Switching Time Measurement Circuit

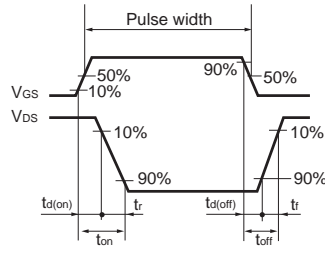


Fig.1-2 Switching Waveforms

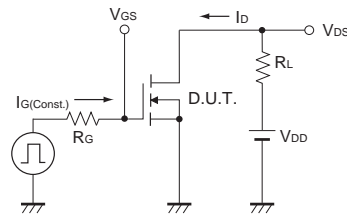


Fig.2-1 Gate Charge Measurement Circuit

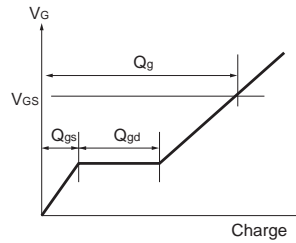


Fig.2-2 Gate Charge Waveform

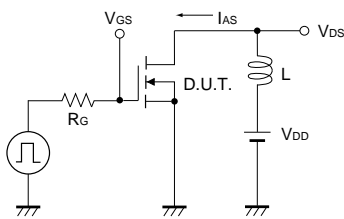


Fig.3-1 Avalanche Measurement Circuit

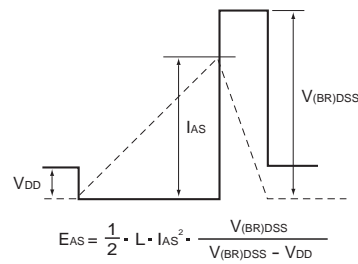


Fig.3-2 Avalanche Waveform

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